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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of _____: July 23, 2003
Christopher Jahnes, et al. : Group Art Unit:
Serial No. 10/604,278 : Examiner:
Filed: 7/8/2003 : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: NOBLE METAL CONTACTS FOR MICRO-ELECTROMECHANICAL SWITCHES

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450


Sir:

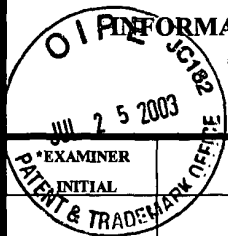
Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the prior patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
David R. Hanson, et al.

By 
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**INFORMATION DISCLOSURE CITATION***(Use several sheets if necessary)*

Docket Number (Optional)

FIS920030061US1

Application Number

10/604,278

Applicant(s)

Hariklia Deligianni, et al.

Filing Date

7/8/03

Group Art Unit

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

"RF Mems Switches adn Switch Circuits" Gabriel M. Rebeiz, Jeremy B. Muldavin, IEEE Microwave Magazine, December 2001 pages 59-71

"(Ba,Sr) TiO3 dielectrics for future stacked-capacitor DRAM" by D.E. Kotecki, J.D. Baniecki, H. Shen, R.B. Laibowitz, K.L. Saenger, J.J. Lian, T.M. Shaw, S.D. Athavale, C. Cabral, Jr., P.R. Duncombe, M. Gutsche, G. Kunkel, Y.-J. Park, Y.-Y. Wang, R. Wise, IBM J. Res, Develop. Vol 43 No. 3 May 1999

IBM Patent Application Number 60/339,089, filed 12/10/01, Christopher Jahnes, et al.

EXAMINER**DATE CONSIDERED**

***EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.